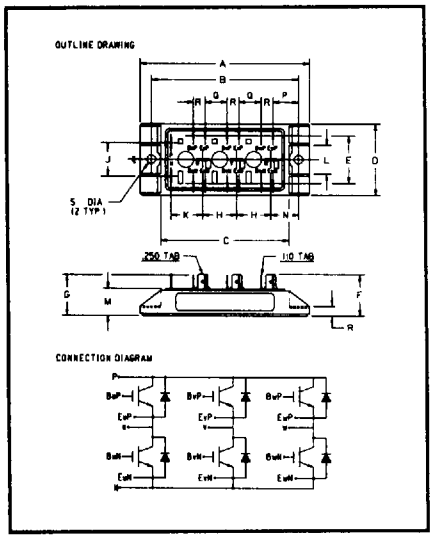
CM30TF-12E

Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

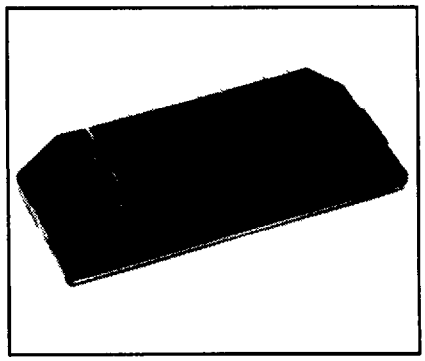
POWEREX INC

Six-IGBT IGBTMOD™ E-Series Module
30 Amperes/600 Volts



CM30TF-12E
Outline Drawing

Dimensions	Inches	Millimeters
A	4.21	107.0
B	3.66±0.01	93.0±0.3
C	3.19	81.0
D	1.77	45.0
E	1.18	30.0
F	1.04	26.5
G	1.01	28.2
H	0.85	21.5
J	0.83	21.0
K	0.79	20.0
L	0.71	18.0
M	0.69±0.02	17.5±0.5
N	0.69	17.5
P	0.63	16.0
Q	0.55	14.0
R	0.30	7.5
S	0.22 Dia.	Dia. 5.5



CM30TF-12E
Six-IGBT IGBTMOD™ E-Series Module
30 Amperes/600 Volts

Description:
Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of six IGBT Transistors in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:
- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery (150ns) Free-Wheel Diode
- ☐ High Frequency Operation (15-20kHz)
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:
- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information:
Example: Select the complete part module number you desire from the table below
-i.e. CM30TF-12E is a 600V (V_{CES}), 30 Ampere Six-IGBT IGBTMOD™ Power Module.

Type	Current Rating Amperes (30)	V_{CES} Volts (x 50)
CM	30	12

http://store.iiic.cc/

Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

CM30TF-12E
Six-IGBT IGBTMOD™ E-Series Module
30 Amperes/600 Volts

Absolute Maximum Ratings, T_j = 25 °C unless otherwise specified

Ratings	Symbol	CM30TF-12E	Units
Junction Temperature	T_j	–40 to 150	°C
Storage Temperature	T_{stg}	–40 to 125	°C
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	600	Volts
Gate-Emitter Voltage	V_{GES}	±20	Volts
Collector Current	I_C	30	Amperes
Peak Collector Current	I_{CM}	60*	Amperes
Diode Forward Current	I_{FM}	30	Amperes
Diode Forward Surge Current	I_{FM}	60*	Amperes
Power Dissipation	P_d	150	Watts
Max. Mounting Torque M5 Mounting Screws	–	17	in-lb
Module Weight (Typical)	–	260	Grams
V Isolation	V_{RMS}	2500	Volts

* Pulse width and repetition rate should be such that device junction temperature does not exceed the device rating

Static Electrical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, V_{GE} = 0V	–	–	1.0	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}$, V_{CE} = 0V	–	–	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	I_C = 3mA, V_{CE} = 10V	3.5	5.0	6.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 30A, V_{GE} = 15V	–	2.7	3.5**	Volts
		I_C = 30A, V_{GE} = 15V, T_j = 150°C	–	2.7	–	Volts
Total Gate Charge	Q_G	V_{CC} = 300V, I_C = 30A, V_{GS} = 15V	–	130	–	nC
Diode Forward Voltage	V_{FM}	I_E = 30A, V_{GS} = 0V	–	–	2.5	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible

Dynamic Electrical Characteristics, T_j = 25 °C unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance		C_{ies}	V_{GE} = 0V, V_{CE} = 10V, f = 1MHz	–	–	5.0	nF
Output Capacitance		C_{oes}		–	–	1.5	nF
Reverse Transfer Capacitance		C_{res}		–	–	1.0	nF
Resistive Load Switch Times	Turn-on Delay Time	$t_{d(on)}$	V_{CC} = 300V, I_C = 25A, $V_{GE1} = V_{GE2}$ = 15V, R_G = 21Ω	–	–	100	ns
	Rise Time	t_r		–	–	200	ns
	Turn-off Delay Time	$t_{d(off)}$		–	–	200	ns
	Fall Time	t_f		–	–	350	ns
Diode Reverse Recovery Time		t_{rr}	I_E = 30A, di_E/dt = –60A/μs	–	–	200	ns
Diode Reverse Recovery Charge		Q_{rr}	I_E = 30A, di_E/dt = –60A/μs	–	0.3	–	μC

Thermal and Mechanical Characteristics, T_j = 25 °C unless otherwise specified

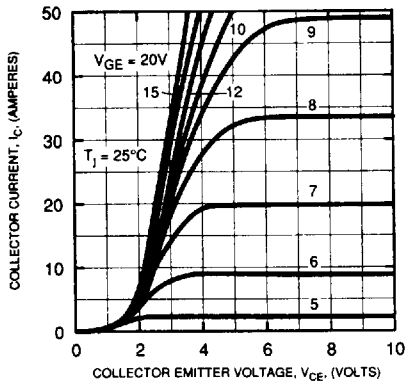
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	–	–	0.80	°C/W
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per Free Wheel Diode	–	–	2.00	°C/W
Contact Thermal Resistance	$R_{th(c-f)}$	Per 1/6 Module	–	–	0.35	°C/W

http://store.iiic.cc/

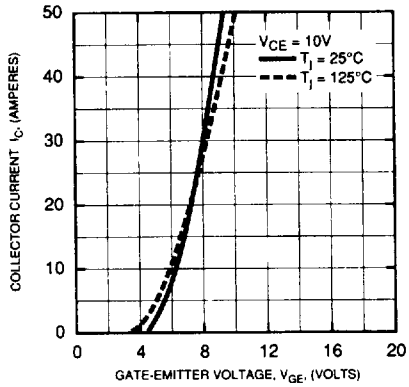
Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

CM30TF-12E
Six-IGBT IGBTMOD™ E-Series Module
30 Amperes/600 Volts

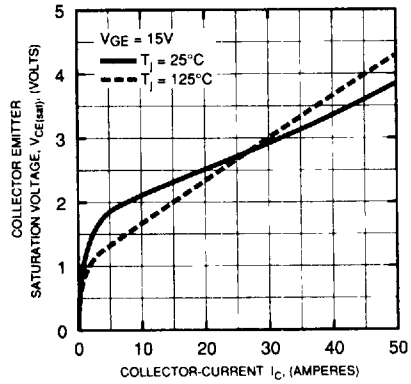
OUTPUT CHARACTERISTICS (TYPICAL)



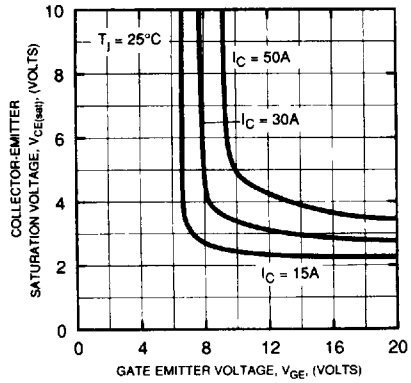
TRANSFER CHARACTERISTICS (TYPICAL)



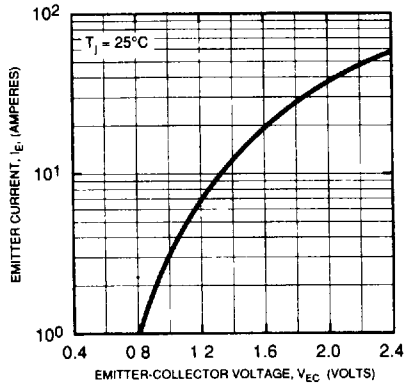
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



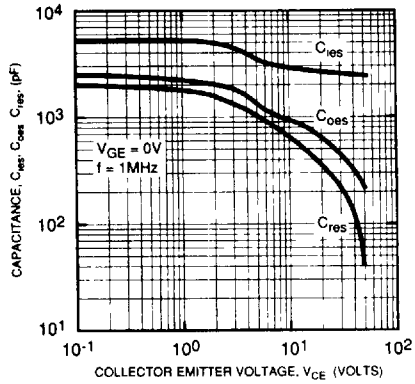
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



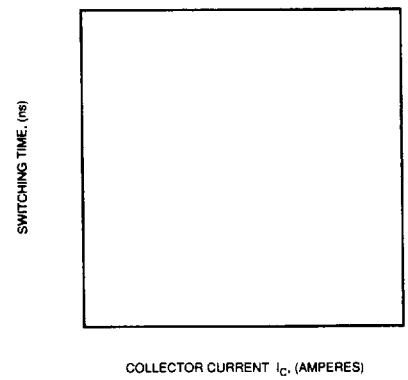
FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)



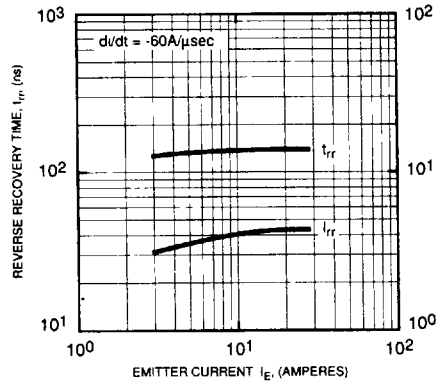
CAPACITANCE VS. V_{CE} (TYPICAL)



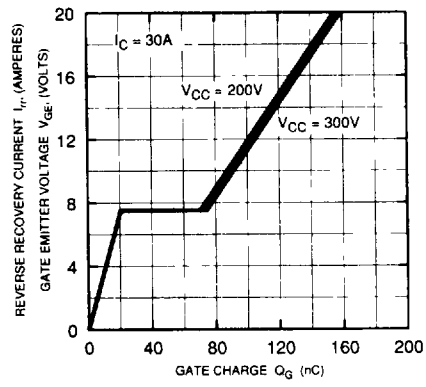
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



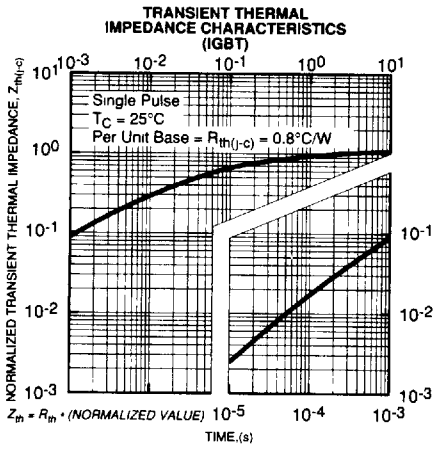
GATE CHARGE, V_{GE}

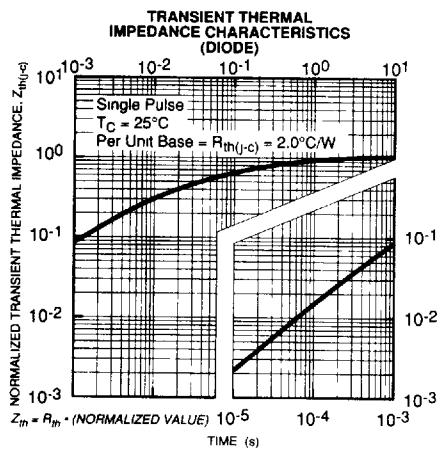


http://store.iiic.cc/

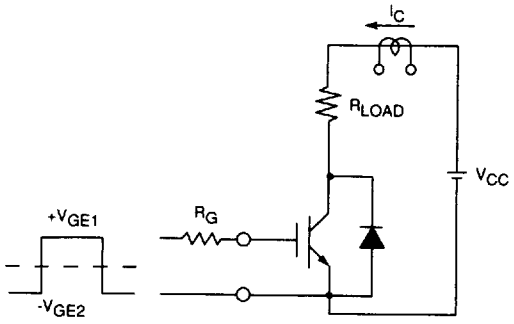
Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

CM30TF-12E
Six-IGBTMOD™ E-Series Module
30 Amperes/600 Volts

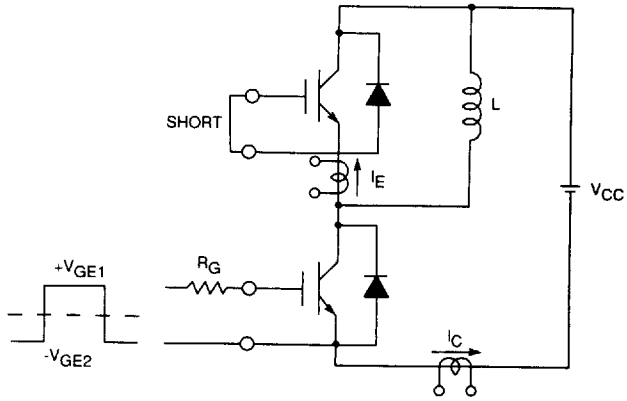




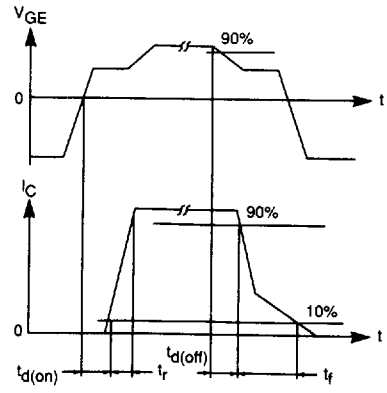
SWITCHING TIME TEST CIRCUITS & WAVEFORMS



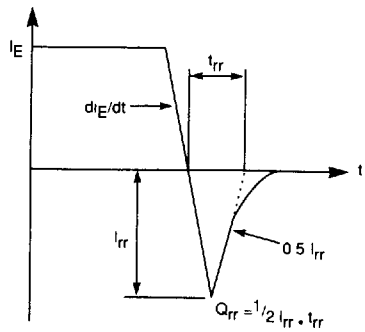
RESISTANCE LOAD SWITCHING TEST CIRCUIT



HALF-BRIDGE SWITCHING TEST CIRCUIT



SWITCHING TIME TEST WAVEFORMS



trr,Qrr WAVEFORMS

http://store.iiic.cc/